

#### **Features**

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Operating temperature range 55 ℃ to 110 ℃
- Regulatory Approvals
  - UL UL1577 (E364000)
  - VDE EN60747-5-5(VDE0884-5)
  - CQC GB4943.1, GB8898
  - IEC60065, IEC60950

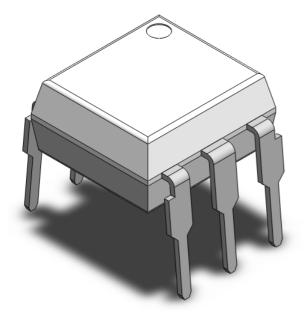
#### **Applications**

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

### **Description**

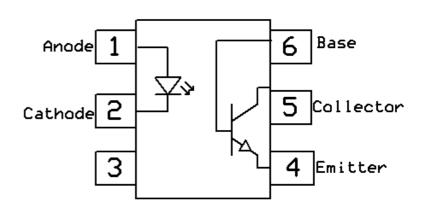
The 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5 series consists of a photo transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 6-lead DIP package different lead forming options.

### **Package Outline**



Note: Different bending options available. See package dimension.

#### **Schematic**





### Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	5000	V <sub>RMS</sub>	
Topr	Operating temperature	-55 ~ +110	°C	
Тѕтс	Storage temperature	-55 ~ +150	°C	
Tsol	Soldering temperature	260	°C	
Emitter		<u>'</u>		
l <sub>F</sub>	Forward current	60	mA	
I <sub>F(TRANS)</sub>	Peak transient current (≤1µs P.W,300pps)	1	А	
VR	Reverse voltage	6	V	
P <sub>D</sub>	Power dissipation	100	mW	
Detector				
P <sub>D</sub>	Power dissipation	150	mW	
Bvceo	Collector-Emitter Breakdown Voltage	80	V	
Вусво	Collector-Base Breakdown Voltage	80	V	
Bveco	Emitter-Collector Breakdown Voltage	7	V	
B <sub>VEBO</sub>	Emitter-Base Breakdown Voltage	7	V	



### **Electrical Characteristics** $T_A = 25 \, ^{\circ}\text{C}$ (unless otherwise specified)

#### **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I <sub>F</sub> =10mA		1.24	1.4	٧	
IR	Reverse Current	V <sub>R</sub> = 6V		-	5	μΑ	
C <sub>IN</sub>	Input Capacitance	f= 1MHz	-	45	-	pF	

#### **Detector Characteristics**

Symbol	Pa	rameters	Test Conditions	Min	Тур	Max	Units	Notes
Bvceo	Collector-Emitter I	Breakdown	Ic= 0.1mA	80	-	-	٧	
Bveco	Emitter-Collector B	Breakdown	I <sub>E</sub> = 0.1mA	7	-	-	٧	
Вусво	Collector-Base Bro	eakdown	Ic= 0.1mA	80	-	-	٧	
B <sub>VEBO</sub>	Emitter-Base Brea	akdown	I <sub>E</sub> = 0.1mA	7	-	-	٧	
Iceo	Collector-Emitter Dark Current	4N25,4N26,4N27,4N28 H11A1,A2,A3,A4,A5	V <sub>CE</sub> = 10V, I <sub>F</sub> =0mA	-	-	50	nA	
		4N35,4N36,4N37,4N38	V <sub>CE</sub> =60V, I <sub>F</sub> =0mA	-	-	50	nA	
Ісво	Collector-Base Da	ark Current	V <sub>CB</sub> = 10V, I <sub>F</sub> =0mA	-	-	20	nA	

#### **Transfer Characteristics**

Symbol	Parameters		Test Conditions	Min	Тур	Max	Units	Notes	
		4N35		100	-	-			
		4N25,4N26, 4N38,		00					
		H11A2, H11A3	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 10V		20	-	-		
OTD	Current	4N27, 4N28, H11A4		10	-	-	% -		
CTR	Transfer	H11A1		50	-	-			
	Ratio	H11A5		30	-	-			
	4N36 4N37	4N36	L 0 A W 5V	130	-	260			
		4N37	I <sub>F</sub> = 2mA, V <sub>CE</sub> = 5V	200	-	400			
	Collector-E	4N25,4N26, 4N27,4N28	I <sub>F</sub> = 50mA, I <sub>C</sub> = 2mA	-	-	0.5			
	mitter	4N35,4N36,4N37		-	-	0.3			
V <sub>CE</sub> (SAT)	Saturation Voltage	H11A1,H11A2, H11A3,H11A4,H11A5	$I_{F}$ = 10mA, $I_{C}$ = 0.5mA	-	-	0.4	V		
		4N38	I <sub>F</sub> = 20mA, I <sub>C</sub> = 4mA	-	-	1.0			



#### **Transfer Characteristics**

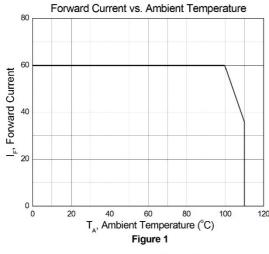
R <sub>IO</sub>	Isolation Resistance	V <sub>IO</sub> = 500V <sub>DC</sub>	1x10 <sup>11</sup>		Ω	
Cıo	Isolation Capacitance	f= 1MHz		0.25	pF	

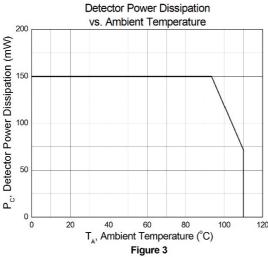
### **Switching Characteristics**

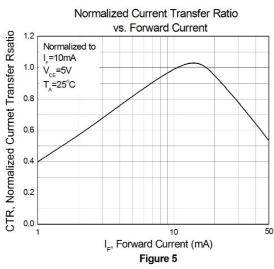
Symbol	F	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
		4N25,4N26,4N27,4N28	I <sub>F</sub> = 10mA, V <sub>CC</sub> = 10V, R <sub>L</sub> =		4.3	9.8		
+	Turn On	H11A1,A2,A3,A4,A5	H11A1,A2,A3,A4,A5 100Ω	,	4.3			
ton	Time	4N35,4N36,4N37,4N38	$I_{c}$ = 2mA, $V_{CC}$ = 10V, $R_{L}$ =		9.8	11.5	μs	
	41/35,41/36,41/37,41/38 100Ω	100Ω	-	3.0	11.5			
		4N25,4N26,4N27,4N28	I <sub>F</sub> = 10mA, V <sub>CC</sub> = 10V, R <sub>L</sub> =		3.9	9.8		
+	Turn Off	H11A1,A2,A3,A4,A5	100Ω	-	3.9	9.0		
t <sub>off</sub>	Time	4N25 4N26 4N27 4N29	I <sub>c</sub> = 2mA, V <sub>CC</sub> = 10V, R <sub>L</sub> =	- 6.9	0.0	0 44.5	μs	
		4N35,4N36,4N37,4N38	100Ω		11.5			

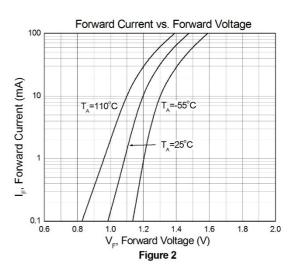


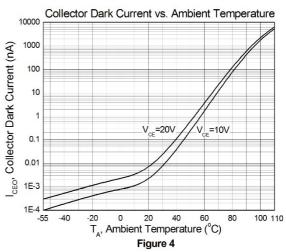
### **Typical Characteristic Curves**

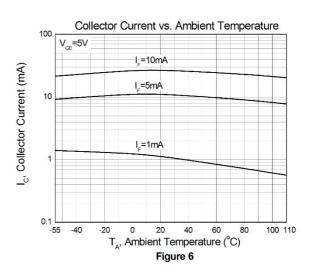




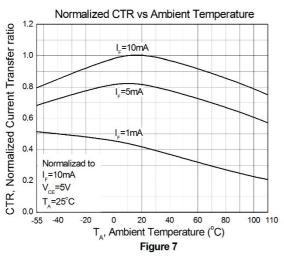


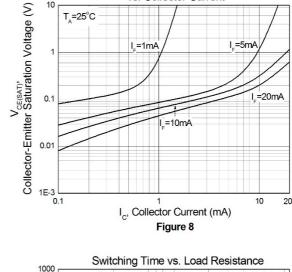






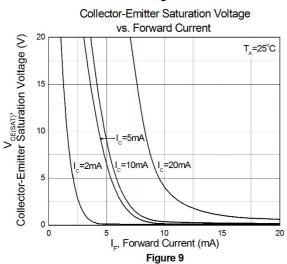


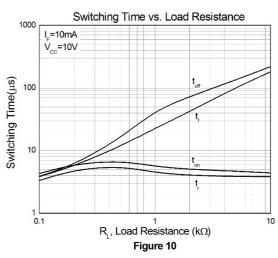


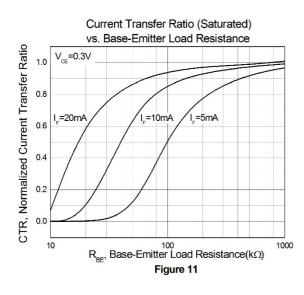


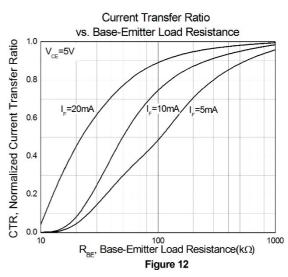
Collector-Emitter Stauration Voltage

vs. Collector Current

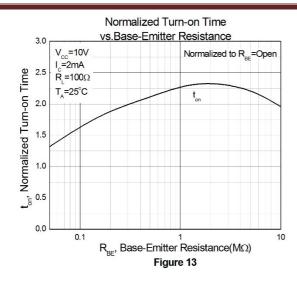


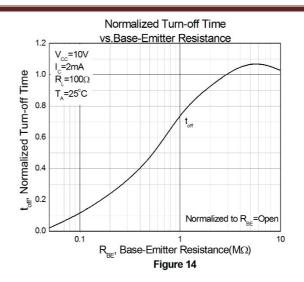








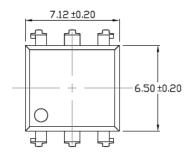


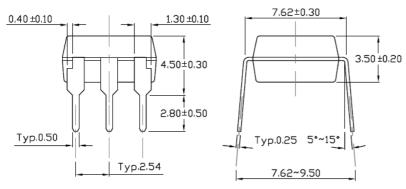




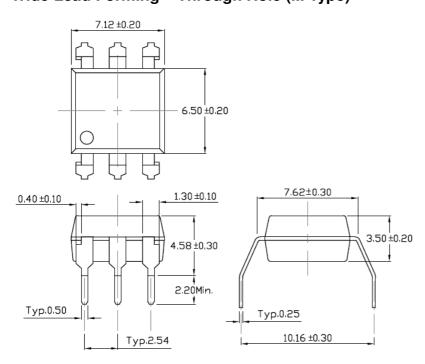
### Package Dimension Dimensions in mm unless otherwise stated

### Standard DIP - Through Hole



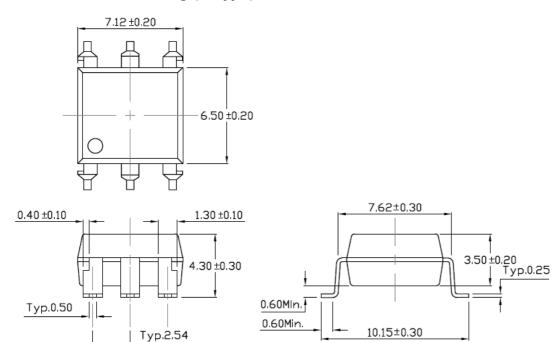


#### Wide Lead Forming – Through Hole (M Type)

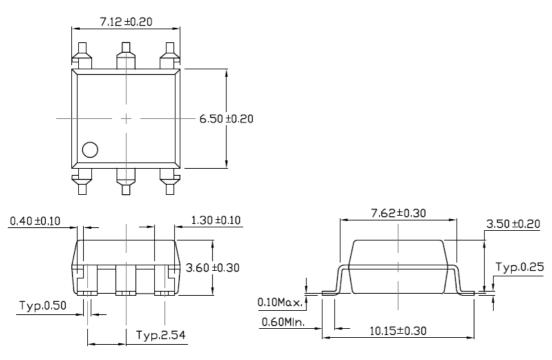




#### **Surface Mount Forming (S Type)**

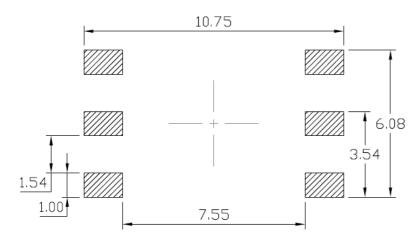


#### **Surface Mount Forming (Low Profile) (SL Type)**

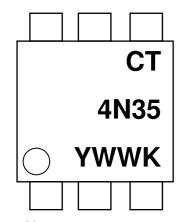




### Recommended Solder Mask Dimensions in mm unless otherwise stated



### **Marking Information**



#### Note:

CT : Denotes "CT Micro"

4N35 : Part Number
Y : Fiscal Year
WW : Work Week

K : Manufacturing Code



### **Ordering Information**

4N2X(Y)(Z)-G, 4N3X(Y)(Z)-G, H11AX(Y)(Z)-G

X = Part No.

(4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5)

Y = Lead form option (S, SL, M or none)

Z = Tape and reel option (T1, T2 or none)

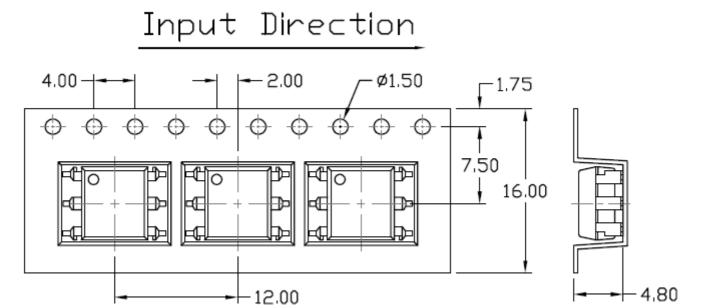
G= Material option (G: Green, None: Non-green)

Option	Description	Quantity
None	Standard 6 Pin Dip	50Units/Tube
М	Wide Lead Forming	50Units/Tube
S(T1)	Surface Mount Lead Forming – With Option A Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option B Taping	1000 Units/Reel
SL(T1)	Surface Mount Lead Forming(Low Profile) – With Option A Taping	1000 Units/Reel
SL(T2)	Surface Mount Lead Forming(Low Profile) – With Option B Taping	1000 Units/Reel



### Carrier Tape Specifications Dimensions in mm unless otherwise stated

Option S(T1) & SL(T1)

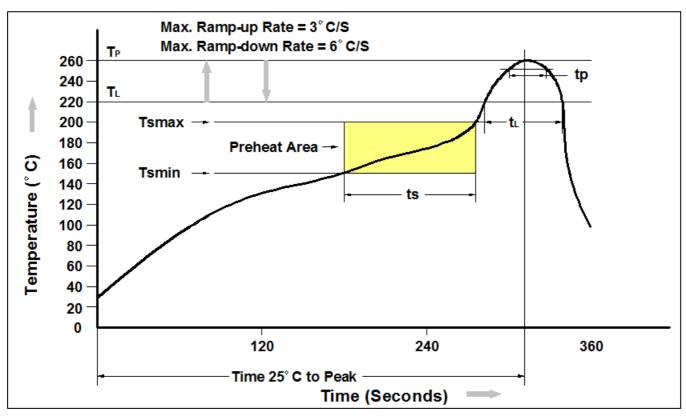


#### Option S(T2) & SL(T2)

# 



#### **Reflow Profile**



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150℃
Temperature Max. (Tsmax)	200℃
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3℃/second max.
Liquidous Temperature (T <sub>L</sub> )	217℃
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260℃ +0℃ / -5℃
Time (t <sub>P</sub> ) within 5 °C of 260 °C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25℃ to Peak Temperature	8 minutes max.



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